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THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Issue Date March 14, 2006 Application Serial No.10/688,439 Filing Date......October 16, 2003 Assignee Micron Technology, Inc. Inventorship......Trung Tri Doan et al. Attorney's Docket No.MI22-2416

Title: Methods of Forming Trench Isolation Regions

REQUEST FOR CERTIFICATE OF CORRECTION OF PATENT FOR APPLICANT MISTAKE and PTO MISTAKES (37 C.F.R. §§ 1.322(a) and 1.323)

To:

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

ATTN:

Decision and Certificate of Correction

Branch of the Patent Issue Division

Certificate

From:

Mark S. Matkin (Tel. 509-624-4276; Fax 509-838-342 1 2006

Wells St. John P.S.

601 W. First Avenue, Suite 1300

of Correction

Spokane, WA 99201-3828

Sir:

It is hereby requested that a Certificate of Correction be issued with respect to Patent No. 7,012,010 B2, granted March 14, 2006, in accordance with the Certificate of Correction form attached hereto in duplicate.

It is noted that an error introduced by the patentee appears in this patent of a typographical nature. Such error occurred in good faith. Correction thereof does not involve such changes in the patent as would constitute new matter or would require re-examination. The exact page and line number where such error occurs in the application file is:

00000005 7012010 11/30/2006 ATRINH

100.00 OP

Preliminary Amendment filed October 16, 2003, page 7, claim 68/ Issued Patent, col. 8, line 10, claim 5.

Other errors listed on the Certificate of Correction form were apparently

incurred through the fault of the PTO as will be disclosed by the records of files

in the Office.

Applicant respectfully refers to the November 25, 2005 Notice of

Allowance where claims 65-68 and 107-125 are indicated to be allowed.

However, in the issued patent only claims 1-5 (previously claims 65-68) are

indicated. Claims 107-125 (issued claims 6-24) have been completely omitted

from the issued patent. Applicant respectfully requests claims 6-24 be inserted

in the issued patent by way of a Certificate of Correction.

Attached hereto, in duplicate, is Form PTO-1050, with at least one copy

being suitable for printing.

Enclosed is a check in the amount of \$100.00, as required by 37 CFR

1.20(a).

Respectfully submitted,

Dated: 11-27-06

Reg. No. 32,268

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO.

: US 7,012,010 B2

ISSUED

: March 14, 2006

APPLICATION NO.: 10/688,439

INVENTOR

: Trung Tri Doan et al.

It is certified that an error or errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col. 5, line 21 -

Replace "O₃ and 88% O₂, at 4000 sccm and helium at from 014 200" With -- O₃ and 88% O₂, at 4000 sccm and helium at from 0-200--

Col. 8, line 18, claim 5 –

Replace "powers an aspect ratio of the trench from what is was prior" With --lowers an aspect ratio of the trench from what it was prior --

Please insert the following claims:

- --6. The method of claim 1 comprising solidifying material of the initially liquid deposition prior to the subsequent initially solid deposition.
- 7. The method of claim 1 wherein the initially liquid deposition and the initially solid deposition occur at different temperatures.
- 8. The method of claim 7 wherein the initially liquid deposition is conducted at temperature lower than that of the initially solid deposition.
- 9. The method of claim 1 comprising annealing the material of the initially liquid deposition prior to the subsequent initially solid deposition.
- 10. The method of claim 9 wherein the annealing is effective to solidify the material of the initially liquid deposition prior to the subsequent initially solid deposition.

Page 1 of 3

Mailing Address of Sender:

Mark S. Matkin Wells St. John P.S. 601 West First Avenue, Suite 1300 Spokane, WA 99201-3828

Patent No. <u>US 7,012,010 B2</u>

DEC - 5 2006

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CERTIFICATE OF CORRECTION

PATENT NO. : US 7,012,010 B2

ISSUED : March 14, 2006

APPLICATION NO.: 10/688,439

INVENTOR : Trung Tri Doan et al.

It is certified that an error or errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

- 11. The method of claim 1 wherein the initially liquid deposition comprises introducing SiH₄ and H₂O₂ into a chamber within which the semiconductive substrate is received.
- **12**. The method of claim **1** wherein the initially liquid deposition comprises introducing SiH₄, H₂O₂, and N₂ into a chamber within which the semiconductive substrate is received.
- 13. The method of claim 1 wherein the initially liquid deposition comprises introducing $(CH_3)_zSiH_{4-z}$ and H_2O_2 into a chamber within which the semiconductive substrate is received, where z is at least 1 and no greater than 4.
 - 14. The method of claim 13 wherein the (CH₃)_zSiH_{4-z} comprises CH₃SiH₃.
- **15**. The method of claim **1** wherein material of the initially liquid deposition deposits over a base of the isolation trench faster than over sidewalls of the isolation trench.
- **16**. The method of claim **1** wherein material of the initially liquid deposition deposits over a base of the isolation trench thicker than over sidewalls of the isolation trench.
- 17. The method of claim 1 comprising exposing material of the initially liquid deposition to ultraviolet light prior to the subsequent initially solid deposition.

Page 2 of 3

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Patent No. <u>US 7,012,010 B2</u>

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CERTIFICATE OF CORRECTION

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ISSUED : March 14, 2006

APPLICATION NO.: 10/688,439

INVENTOR : Trung Tri Doan et al.

It is certified that an error or errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

- 18. The method of claim 17 comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to ultraviolet light.
- 19. The method of claim 1 comprising exposing material of the initially liquid to an electron beam prior to the subsequent initially solid deposition.
- 20. The method of claim 19 comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to the electron beam.
- 21. The method of claim 1 comprising exposing material of the initially liquid to a plasma prior to the subsequent initially solid deposition.
- 22. The method of claim 21 comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to plasma.
- 23. The method of claim 1 comprising exposing material of the initially liquid deposition to RF energy prior to the subsequent initially solid deposition.
- 24. The method of claim 23 comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to RF energy.--

Page 3 of 3

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Mark S. Matkin Wells St. John P.S. 601 West First Avenue, Suite 1300 Spokane, WA 99201-3828 Patent No. <u>US 7,012,010 B2</u>

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Col. 8, line 18, claim 5 -

Replace "powers an aspect ratio of the trench from what is was prior" With --lowers an aspect ratio of the trench from what it was prior --

Please insert the following claims:

- --6. The method of claim 1 comprising solidifying material of the initially liquid deposition prior to the subsequent initially solid deposition.
- 7. The method of claim 1 wherein the initially liquid deposition and the initially solid deposition occur at different temperatures.
- 8. The method of claim 7 wherein the initially liquid deposition is conducted at temperature lower than that of the initially solid deposition.
- 9. The method of claim 1 comprising annealing the material of the initially liquid deposition prior to the subsequent initially solid deposition.
- 10. The method of claim 9 wherein the annealing is effective to solidify the material of the initially liquid deposition prior to the subsequent initially solid deposition.

Page 1 of 3

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Mark S. Matkin Wells St. John P.S. 601 West First Avenue, Suite 1300 Spokane, WA 99201-3828 Patent No. <u>US 7,012,010 B2</u>

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It is certified that an error or errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

- 11. The method of claim 1 wherein the initially liquid deposition comprises introducing SiH₄ and H₂O₂ into a chamber within which the semiconductive substrate is received.
- 12. The method of claim 1 wherein the initially liquid deposition comprises introducing SiH_4 , H_2O_2 , and N_2 into a chamber within which the semiconductive substrate is received.
- 13. The method of claim 1 wherein the initially liquid deposition comprises introducing $(CH_3)_zSiH_{4-z}$ and H_2O_2 into a chamber within which the semiconductive substrate is received, where z is at least 1 and no greater than 4.
 - **14**. The method of claim **13** wherein the $(CH_3)_zSiH_{4-z}$ comprises CH_3SiH_3 .
- **15**. The method of claim **1** wherein material of the initially liquid deposition deposits over a base of the isolation trench faster than over sidewalls of the isolation trench.
- **16**. The method of claim **1** wherein material of the initially liquid deposition deposits over a base of the isolation trench thicker than over sidewalls of the isolation trench.
- 17. The method of claim 1 comprising exposing material of the initially liquid deposition to ultraviolet light prior to the subsequent initially solid deposition.

Page 2 of 3

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Patent No. <u>US 7,012,010 B2</u>

IEE - 5 2003

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PATENT NO. : US 7,012,010 B2

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APPLICATION NO.: 10/688,439

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- 18. The method of claim 17 comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to ultraviolet light.
- 19. The method of claim 1 comprising exposing material of the initially liquid to an electron beam prior to the subsequent initially solid deposition.
- 20. The method of claim 19 comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to the electron beam.
- 21. The method of claim 1 comprising exposing material of the initially liquid to a plasma prior to the subsequent initially solid deposition.
- 22. The method of claim 21 comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to plasma.
- 23. The method of claim 1 comprising exposing material of the initially liquid deposition to RF energy prior to the subsequent initially solid deposition.
- 24. The method of claim 23 comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to RF energy.--

Page 3 of 3

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Mark S. Matkin Wells St. John P.S. 601 West First Avenue, Suite 1300 Spokane, WA 99201-3828 Patent No. <u>US 7,012,010 B2</u>

IDEC - 5 2006

PAT-US\CR-01

PTO/SB/17 (07-06)

NON 3 0 5000 Approved for use through 01/31/2007. OMB 0651-0032 U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE Under the Paperwork Reduction Af 1995 no persons are required to respond to a collection of information unless it displays a valid OMB control number Effective on 12/08/2004.
Fees pursuant to the first seed Appropriations Act, 2005 (H.R. 4818). FEE TRANSMITTAL

For FY 2006

Applicant claims small entity status. See 37 CFR 1.27

TOTAL AMOUNT OF PAYMENT (\$)

100.00

Complete if Known				
Application Number	10/688,439 (US Pat 7,012,010)			
Filing Date	Oct. 16, 2006 (Issued 3/14/06)			
First Named Inventor	Trung Tri Doan			
Examiner Name	David S. Blum	•		
Art Unit	2813			
Attorney Docket No.	MI22-2416			

TOTAL AMOUNT OF PAY	/MENT (\$)	100.00	Attorney Dock	et No. MI2	2-2416		
METHOD OF PAYMENT (check all that apply)							
Check Credit Card Money Order None Other (please identify):							
Deposit Account Deposit Account Number: 23-0925 Deposit Account Name: Wells St. John P.S.							
For the above-identified deposit account, the Director is hereby authorized to: (check all that apply)							
Charge fee(s) indicated below Charge fee(s) indicated below, except for the filing fee							
under 37 CF	R 1.16 and 1.17	r underpayments of f		lit any overpay			
WARNING: Information on th information and authorization		e public. Credit card in	nformation should	not be included	l on this form. Pr	ovide credit card	
FEE CALCULATION		· · · · · · · · · · · · · · · · · · ·					
1. BASIC FILING, SEA	•					 	
	FILING FEE Smal	S SEA <u>l Entity</u>	RCH FEES Small Entity		TION FEES Small Entity		
Application Type		e (\$) Fee (\$) Fee (\$)	Fee (\$)	Fee (\$)	Fees Paid (\$)	
Utility	300 1:	50 500	250	200	100	0.00	
Design	200 10	00 100	50	130	65	0.00	
Plant	200 10	300	150	160	80	0.00	
Reissue	300 1:	500	250	600	300	0	
Provisional	200 10	0 0	0	0	0	0.00	
2. EXCESS CLAIM FEES Fee Description Small Entity Fee (\$) Fee (\$)							
Each claim over 20 (including Reiss	ues)			50	25	
Each independent cl	`	•			200	100	
Multiple dependent	claims				360	180	
Total Claims	Extra Claims	<u>Fee (\$) </u>	ee Paid (\$)		Multiple De	pendent Claims	
- 20 or HP = HP = highest number of total		=	0.00		<u>Fee (\$)</u>	Fee Paid (\$)	
Indep. Claims	Extra Claims		e Paid (\$)			0.00	
3 or HP =	x	= <u></u>	0.00 .				
HP = highest number of inde	•	I for, if greater than 3.					
	3. APPLICATION SIZE FEE If the specification and drawings exceed 100 sheets of paper (excluding electronically filed sequence or computer						
listings under 37 CFR 1.52(e)), the application size fee due is \$250 (\$125 for small entity) for each additional 50							
sheets or fraction thereof. See 35 U.S.C. 41(a)(1)(G) and 37 CFR 1.16(s). Total Sheets Extra Sheets Number of each additional 50 or fraction thereof Fee (\$) Fee Paid (\$)							
Total Sheets Extra Sheets Number of each additional 50 or fraction thereof Fee (\$) Fee Paid (\$) - 100 = /50 = (round up to a whole number) x = 0.00							
4. OTHER FEE(S) Non-English Specification, \$130 fee (no small entity discount) Fees Paid (\$) 0.00							

SUBMITTED BY		
Signature Control of the Signature Control of	Registration No. (Attorney/Agent) 32,268	Telephone (509) 624-4276
Name (Prim#Type) Mark S. Matkin		Date 11-27-06

Other (e.g., late filing surcharge): Req. for Certificate of Correction-App error

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This collection of information is required by 37 CFR 1.136. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 30 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

100.00

PTO/SB/17 (07-06)

NOV 3 0 ZUUB

Approved for use through 01/31/2007. OMB 0651-0032

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995 no persont are required to respond to a collection of information unless it displays a valid OMB control number Effective on 12/08/2004.
Fees pursuant to the Consolidates Propopriation 2005 (H.R. 4818). Complete if Known 10/688,439 (US Pat 7,012,010) **Application Number** Filing Date Oct. 16, 2006 (Issued 3/14/06) For FY 2006 First Named Inventor **Examiner Name** Applicant claims small entity status. See 37 CFR 1.27 Art Unit TOTAL AMOUNT OF PAYMENT (\$) 100.00 Attorney Docket No. MI22-2416 **METHOD OF PAYMENT** (check all that apply) Check Credit Card L JMoney Order L None Other (please identify): ✓ Deposit Account Deposit Account Number: 23-0925 Deposit Account Name: Wells St. John P.S. For the above-identified deposit account, the Director is hereby authorized to: (check all that apply) Charge fee(s) indicated below Charge fee(s) indicated below, except for the filing fee Charge any additional fee(s) or underpayments of fee(s) Credit any overpayments under 37 CFR 1.16 and 1.17 WARNING: Information on this form may become public. Credit card information should not be included on this form. Provide credit card information and authorization on PTO-2038. **FEE CALCULATION** 1. BASIC FILING, SEARCH, AND EXAMINATION FEES **FILING FEES** SEARCH FEES **EXAMINATION FEES Small Entity Small Entity** Small Entity **Application Type** Fee (\$) Fee (\$) Fee (\$) Fee (\$) Fees Paid (\$) Fee (\$) Fee (\$) Utility 300 150 500 250 200 100 0.00 Design 200 100 100 50 130 0.00 65 Plant 200 0.00 100 300 150 160 80 Reissue 300 150 500 250 600 300 Provisional 200 100 0 0 0.00 2. EXCESS CLAIM FEES **Small Entity Fee Description** Fee (\$) Fee (\$) Each claim over 20 (including Reissues) 50 25 Each independent claim over 3 (including Reissues) 200 100 Multiple dependent claims 360 180 **Total Claims Extra Claims** Fee (\$) Fee Paid (\$) **Multiple Dependent Claims** Fee (\$) Fee Paid (\$) HP = highest number of total claims paid for, if greater than 20. 0.00 Extra Claims Indep. Claims Fee Paid (\$) - 3 or HP = HP = highest number of independent claims paid for, if greater than 3. 3. APPLICATION SIZE FEE If the specification and drawings exceed 100 sheets of paper (excluding electronically filed sequence or computer listings under 37 CFR 1.52(e)), the application size fee due is \$250 (\$125 for small entity) for each additional 50 sheets or fraction thereof. See 35 U.S.C. 41(a)(1)(G) and 37 CFR 1.16(s). Number of each additional 50 or fraction thereof **Total Sheets Extra Sheets** Fee (\$) Fee Paid (\$) (round up to a whole number) 0.00 4. OTHER FEE(S) Fees Paid (\$) Non-English Specification, \$130 fee (no small entity discount) 0.00 Other (e.g., late filing surcharge): Reg. for Certificate of Correction-100.00

SUBMITTED BY Telephone (509) 624-4276 Signature (Attorney/Agent) Name (Prim Fype) Mark S. Matkin

This collection of information is required by 37 CFR 1.136. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 30 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Under the Paperwork Reduction Act of 1995.	no persons are required to Application	respond to a collection of	PTO/SB/21 (09-06) Approved for use through 03/31/2007. OMB 0651-0031 d Trademark Office; U.S. DEPARTMENT OF COMMERCE information unless it displays a valid OMB control number. 439 (US Pat. No. 7,012,010 B2)		
TRANSMITTAL	Filing Date	October	October 16, 2003 (Issued March 14, 2006)		
FORM	First Named	I Inventor Trung T	ri Doan		
	Art Unit	2813			
(to be used for all correspondence after initial f	Examiner N	ame David S	S. Blum		
		cket Number MI22-24	MI22-2416		
	ENCLOSURES	(Check all that ap	ply)		
Fee Transmittal Form Fee Attached Amendment/Reply After Final Affidavits/declaration(s) Extension of Time Request Express Abandonment Request Information Disclosure Statement Certified Copy of Priority Document(s) Reply to Missing Parts/ Incomplete Application Reply to Missing Parts under 37 CFR 1.52 or 1.53	Change of Cor Terminal Discl Request for Re CD, Number o Landsca Remarks Customer No. 021567	nvert to a plication ney, Revocation respondence Address aimer efund of CD(s) pe Table on CD	After Allowance Communication to TC Appeal Communication to Board of Appeals and Interferences Appeal Communication to TC (Appeal Notice, Brief, Reply Brief) Proprietary Information Status Letter Other Enclosure(s) (please Identify below): PTO Return Receipt Postcard Chk # 152036 for \$100.00 Request for Certificate of Correction-App and PTO errors Certificate of Correction in duplicate		
Firm Name					
Wells St. John P.S.					
Signature	e 111				
Printed name Mark S. Matkin					

CERTIFICATE OF TRANSMISSION/MAILING

I hereby certify that this correspondence is being facsimile transmitted to the USPTO or deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on the date shown below:

Signature

Muriel G. Dunnigan Typed or printed name

32,268

Date | November 27, 2006

This collection of information is required by 37 CFR 1.5. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.11 and1.14. This collection is estimated to 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.